

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D = -250\mu A$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V,$	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS} = -10V, I_D = -12A$	-	8.3	11	m Ω
		$V_{GS} = -4.5V, I_D = -8A$	-	12	15	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.0MHz$	-	1890	-	pF
C_{oss}	Output Capacitance		-	346	-	pF
C_{rss}	Reverse Transfer Capacitance		-	319	-	pF
Q_g	Total Gate Charge	$V_{DS} = -15V, I_D = -20A,$ $V_{GS} = -10V$	-	30	-	nC
Q_{gs}	Gate-Source Charge		-	5.3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	7.6	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -15V, I_D = -20A,$ $V_{GS} = -10V, R_{GEN} = 2.5\Omega$	-	14	-	ns
t_r	Turn-on Rise Time		-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	95	-	ns
t_f	Turn-off Fall Time		-	65	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-55	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-140	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S = -35A$	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J = 25^{\circ}\text{C}$, $V_{DD} = -20V$, $V_G = -10V$, $L = 0.5mH$, $R_G = 25\Omega$, $I_{AS} = -17A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

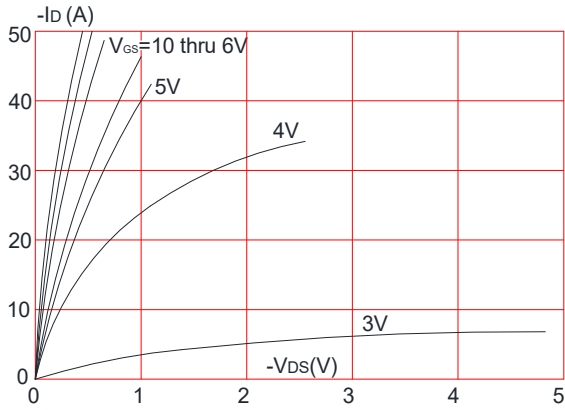


Figure 2: Typical Transfer Characteristics

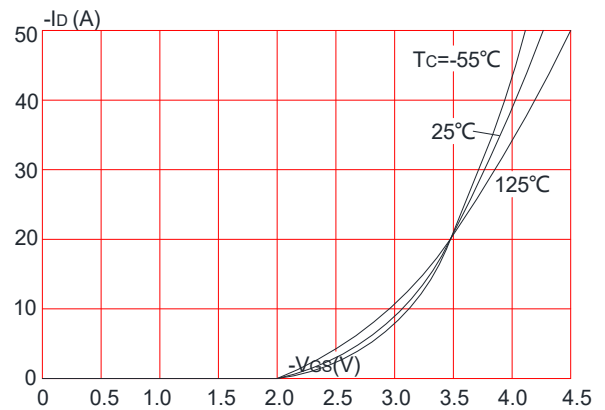


Figure 3: On-resistance vs. Drain Current

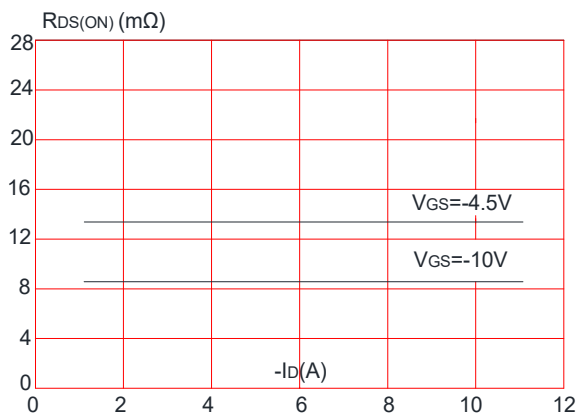


Figure 4: Body Diode Characteristics

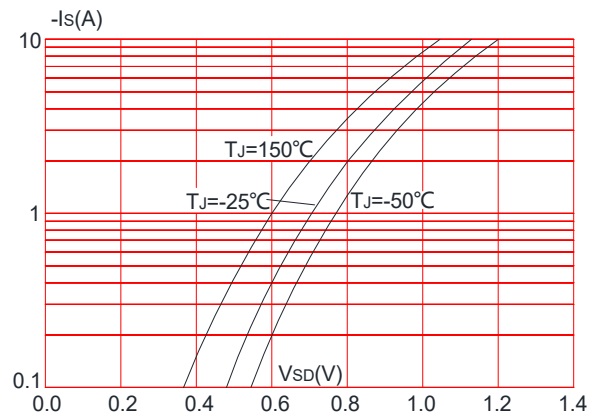


Figure 5: Gate Charge Characteristics

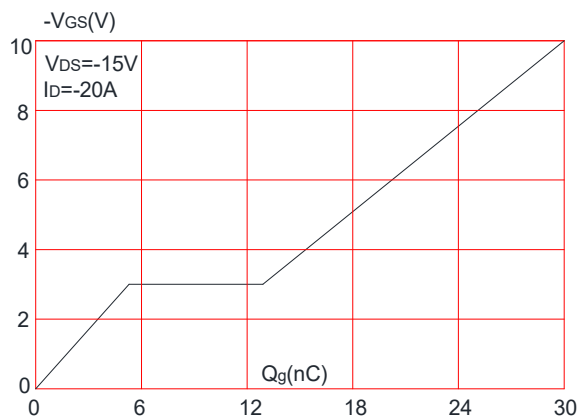


Figure 6: Capacitance Characteristics

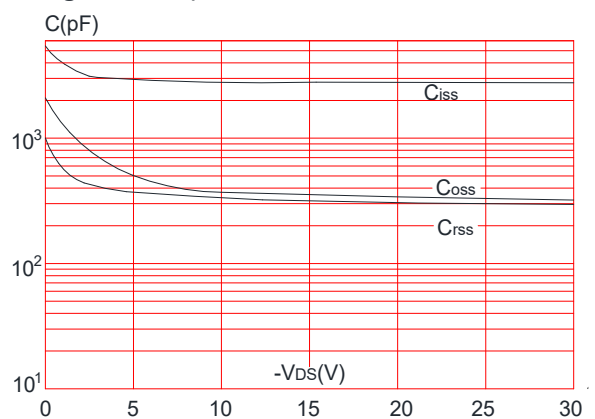


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

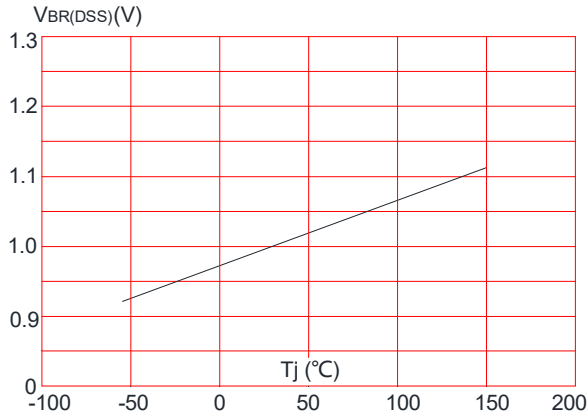


Figure 8: Normalized on Resistance vs. Junction Temperature

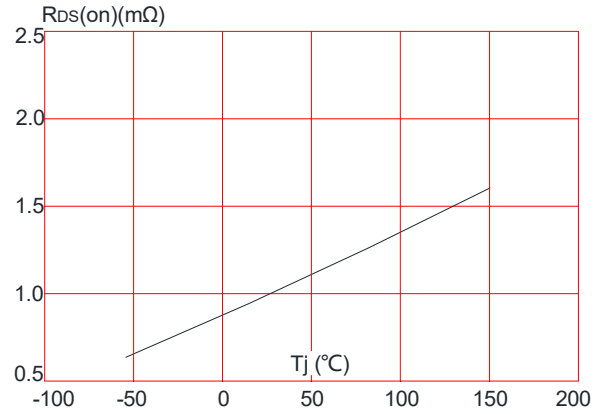


Figure 9: Maximum Safe Operating Area

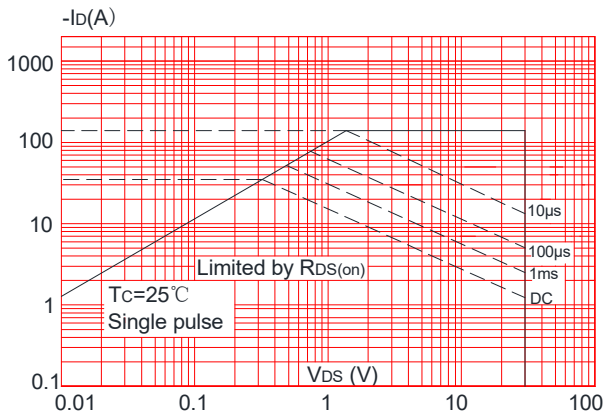


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

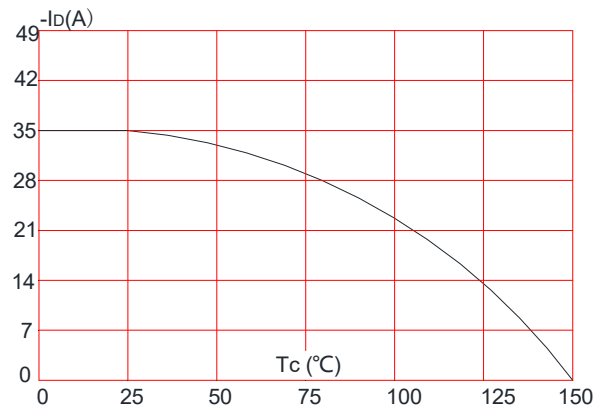
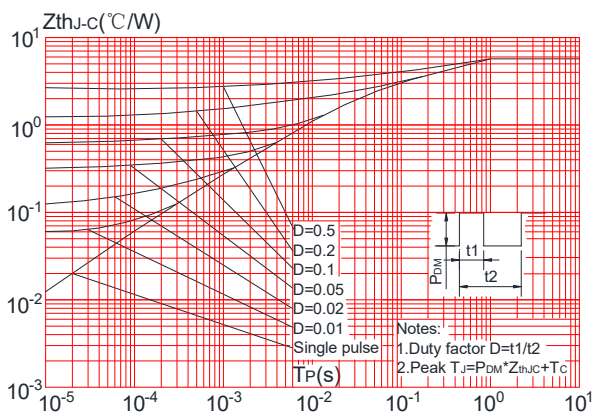
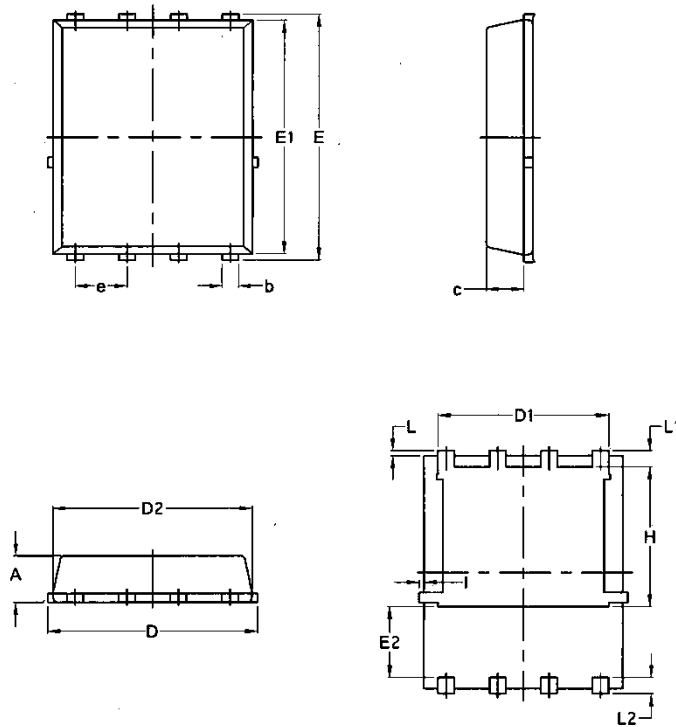


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



3DFNDJH 0HFKDQ'D FQO /DWD



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